NOT RECOMMENDED FOR NEW DESIGN **USE DSS4160T**





LOW $V_{\text{CE(SAT)}}$ NPN SURFACE MOUNT TRANSISTOR

Features

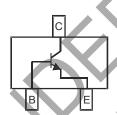
- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (DPLS160)
- Surface Mount Package Suited for Automated Assembly
- Lead Free/RoHS Compliant (Note 1)
- "Green Device" (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)



SOT-23



Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

	W. Carlotte and Ca	0, 4000, 10 W	M 400000 W	
Characteristic		Symbol	Value	Unit
Collector-Base Voltage		V _{CBO}	80	V
Collector-Emitter Voltage		V _{CEO}	60	V
Emitter-Base Voltage		V _{EBO}	5	V
Collector Current - Continuous		l _C	1	Α
Peak Pulse Collector Current		I _{CM}	2	Α
Base Current (DC)		I _B	300	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P_{D}	300	mW
Thermal Resistance, Junction to Ambient (Note 3) @ T _A = 25°C	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- No purposefully added lead.
- Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

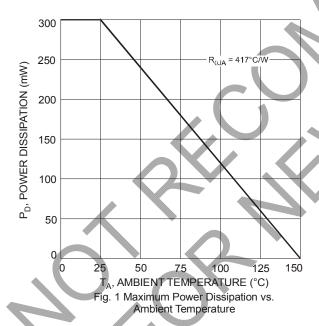
 Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

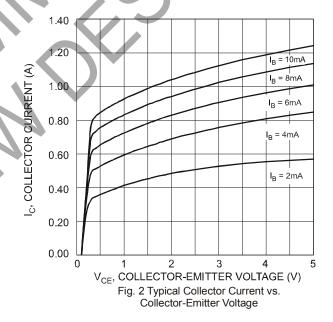


Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	80	_		V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	60	_		٧	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	_		>	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	lone			100	nA	$V_{CB} = 60V, I_{E} = 0$
Concetor Cuton Current	I _{CBO}			50	μΑ	$V_{CB} = 60V$, $I_E = 0$, $T_A = 150$ °C
Collector Cutoff Current	I _{CES}	_	_	100	nA	$V_{CE} = 60V, V_{BE} = 0$
Emitter Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 5V, I_C = 0$
ON CHARACTERISTICS (Note 4)						
		250	320	_		$V_{CE} = 5V$, $I_{C} = 1mA$
DC Current Gain	h _{FE}	200	280	_	V	$V_{CE} = 5V, I_{C} = 500mA$
		100	165	_	,	$V_{CE} = 5V$, $I_C = 1A$
		_	80	110		$I_C = 100 \text{mA}, I_B = 1 \text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	_	80	140	mV	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
		_	140	250		$I_C = 1A$, $I_B = 100mA$
Collector-Emitter Saturation Resistance	R _{CE(SAT)}	_	140	250	mΩ	$I_C = 1A$, $I_B = 100mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}		0.91	1.1	V	$I_C = 1A$, $I_B = 50mA$
Base-Emitter Turn On Voltage	V _{BE(ON)}	_	0.81	0.9	V	$V_{CE} = 5V$, $I_C = 1A$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C_{obo}		7	10	pF 🤚	V _{CB} = 10V, f = 1.0MHz
Current Gain-Bandwidth Product	f _T	150	270		MHz	$V_{CE} = 10V$, $I_{C} = 50$ mA, $f = 100$ MHz

Notes: 4. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.







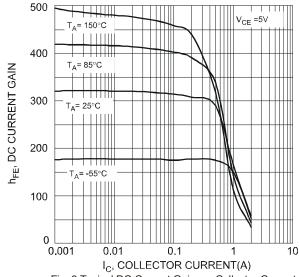
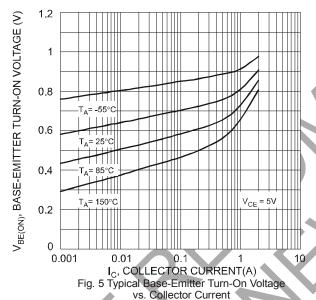


Fig. 3 Typical DC Current Gain vs. Collector Current



120 100 (Lg) 80 80 C_{ibo} C_{ibo} C_{obo} 0 0.1 1 10 100 V_R, REVERSE VOLTAGE (V)

Fig. 7 Typical Capacitance Characteristics

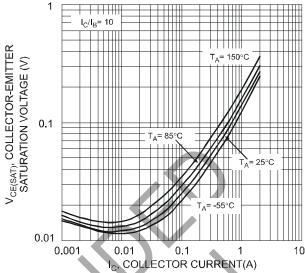


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

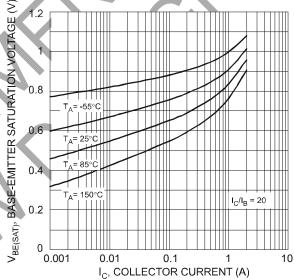
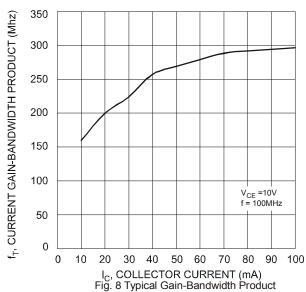


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current



vs. Collector Current

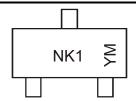


Ordering Information (Note 5)

Device	Packaging	Shipping
DNLS160-7	SOT-23	3000/Tape & Reel

5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



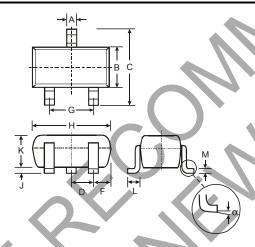
NK1 = Product Type Marking Code YM = Date Code Marking Y = Year ex: V = 2008

M = Month ex: 9 = September

Date Code Key

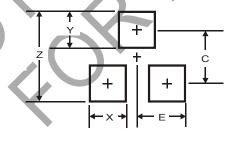
Year	2008		2009	2010		2011	2012	2013	2014	2015
Code	V		W	Х		Υ	Z	А	В	С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul A	ug Sep	Oct N	ov Dec
Code	1	2	3	4	5	6	7	8 9	0	N D

Package Outline Dimensions



SOT-23					
Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
С	2.30	2.50			
D	0.89	1.03			
F	0.45	0.60			
G	1.78	2.05			
Н	2.80	3.00			
J	0.013	0.10			
K	0.903	1.10			
L	0.45	0.61			
М	0.085	0.180			
α	0°	8°			
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35

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